

NPN Darlington Transistor

This device is designed for applications requiring extremely high current gain at collector currents to 500 mA. Sourced from Process 03.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units	
V _{CES}	Collector-Emitter Voltage	80	V	
V _{CBO}	Collector-Base Voltage	80	V	
V _{EBO}	Emitter-Base Voltage	12	V	
I _C	Collector Current - Continuous	800	mA	
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C	

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Мах			Units
		MPSA28	*MMBTA28	**PZTA28	
P _D	Total Device Dissipation Derate above 25°C	625 5.0	350 2.8	1,000 8.0	mW mW/∘C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3			°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	357	125	°C/W

*Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

** Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm².

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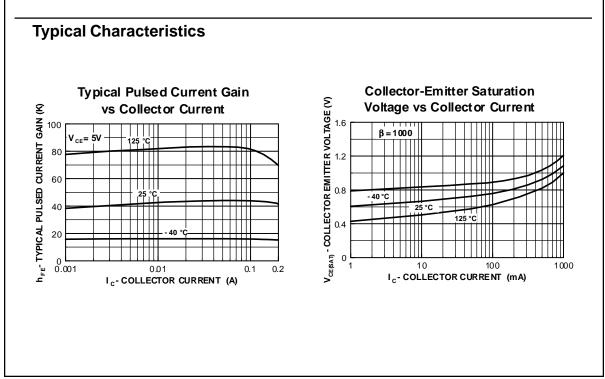
(continued)

Electri	Electrical Characteristics TA=25°C unless otherwise noted					
Symbol	Parameter	Test Conditions	Min	Мах	Units	
OFF CHAI	RACTERISTICS					
V _{(BR)CES}	Collector-Emitter Breakdown Voltage	$I_{C} = 100 \ \mu A, \ V_{BE} = 0$	80		V	
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 100 \ \mu {\rm A}, \ I_{\rm E} = 0$	80		V	
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_{\rm E} = 10 \ \mu A, I_{\rm C} = 0$	12		V	
I _{CBO}	Collector Cutoff Current	$V_{CB} = 60 \text{ V}, I_E = 0$		100	nA	
I _{CES}	Collector Cutoff Current	$V_{CE} = 60 \text{ V}, \text{ V}_{BE} = 0$		500	nA	
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 10 \text{ V}, \text{ I}_{C} = 0$		100	nA	
ON CHAR	ACTERISTICS				-	
h _{FE}	DC Current Gain	$I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_{C} = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$	10,000 10,000			
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_{\rm C} = 10$ mA, $I_{\rm B} = 0.01$ mA $I_{\rm C} = 100$ mA, $I_{\rm B} = 0.1$ mA		1.2 1.5	V	
V _{BE(on)}	Base-Emitter On Voltage	$I_{\rm C}$ = 100 mA, $V_{\rm CE}$ = 5.0 V		2.0	V	

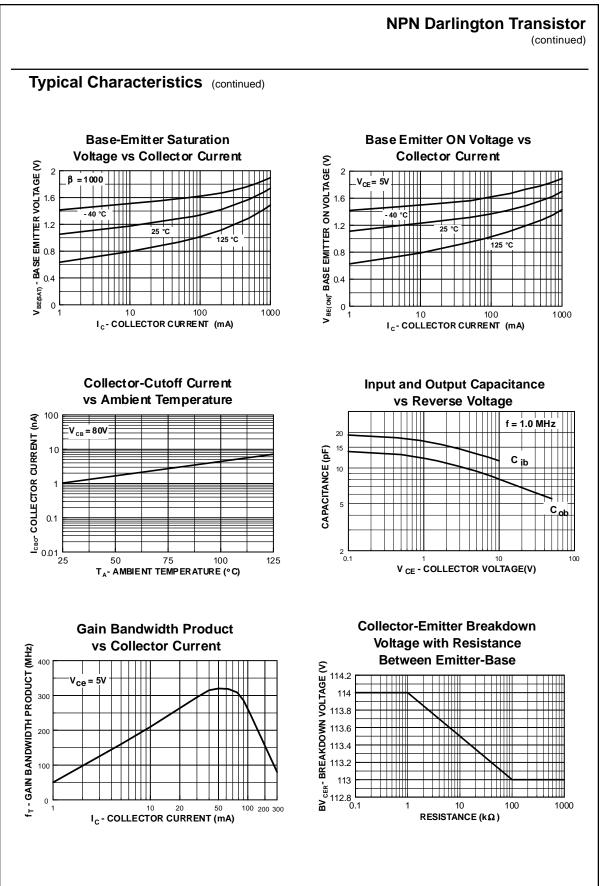
SMALL SIGNAL CHARACTERISTICS

f _T	Current Gain - Bandwidth Product	$I_{C} = 10 \text{ mA}, V_{CE} = 5.0,$ f = 100 MHz	125		MHz
C _{obo}	Output Capacitance	$V_{CB} = 1.0 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$		8.0	pF

*Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%



MPSA28/MMBTA28/PZTA28, Rev A



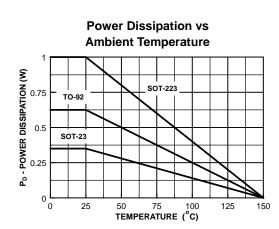
MPSA28/MMBTA28/PZTA28, Rev A

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MPSA28/MMBTA28/PZTA28, Rev A



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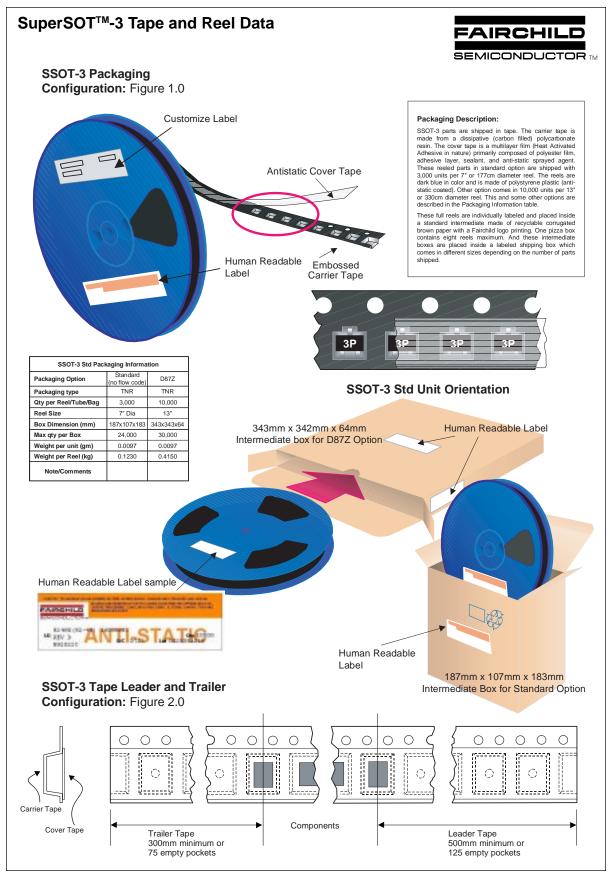
March 2001, Rev. B1





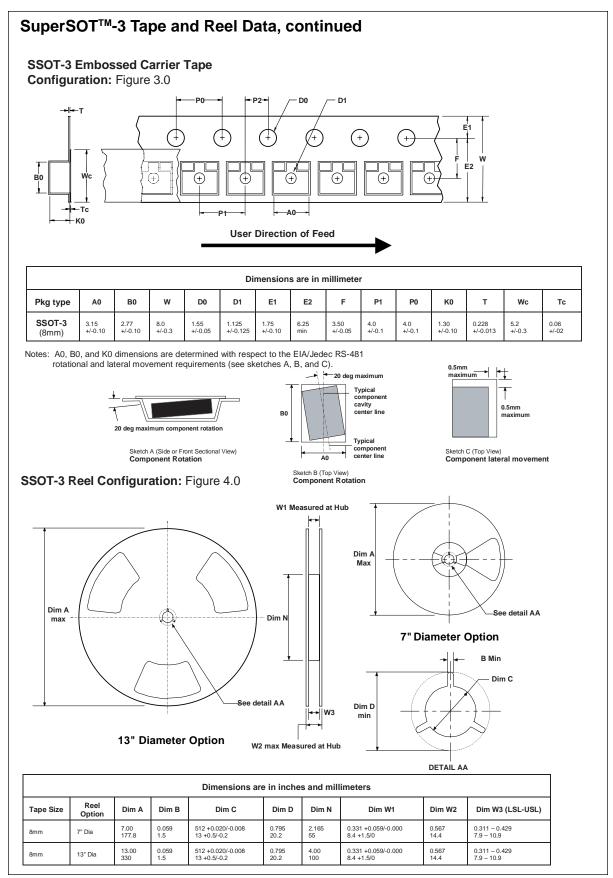
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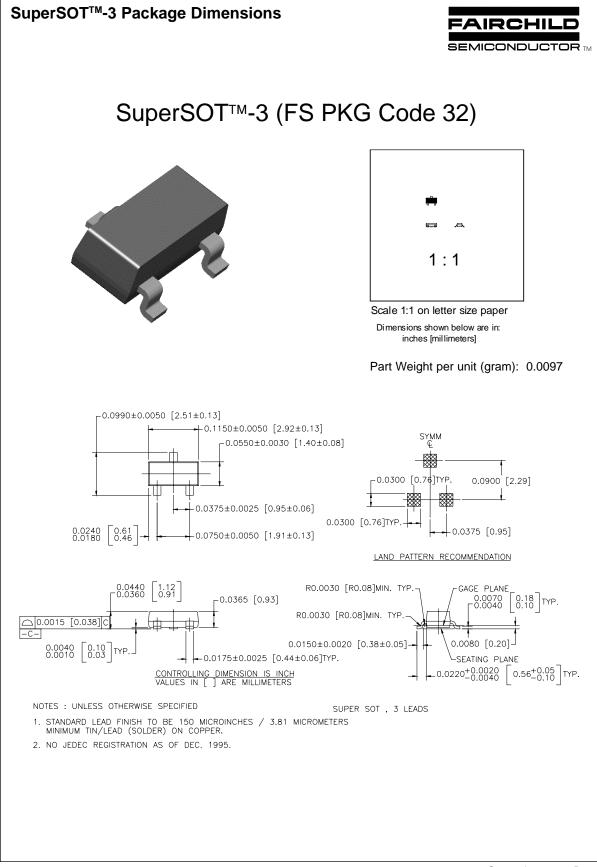


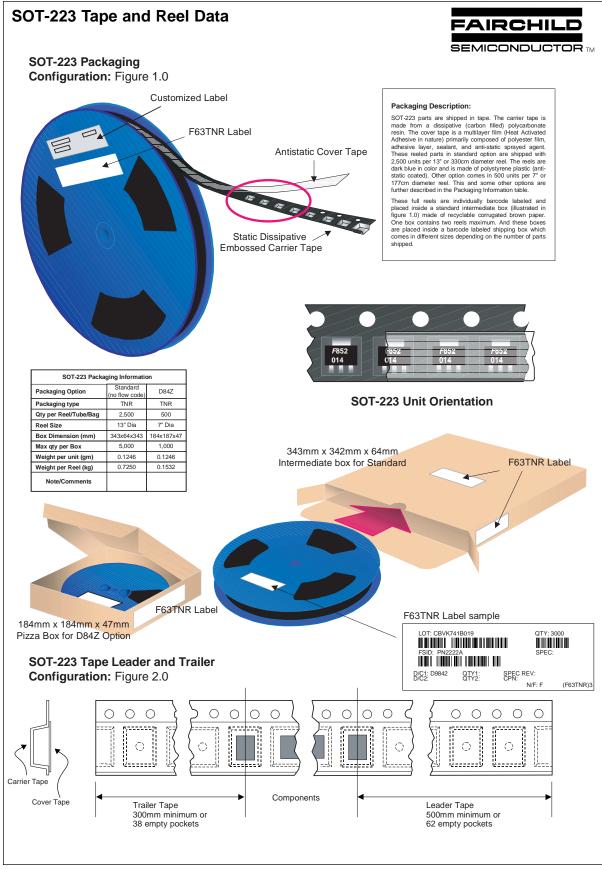
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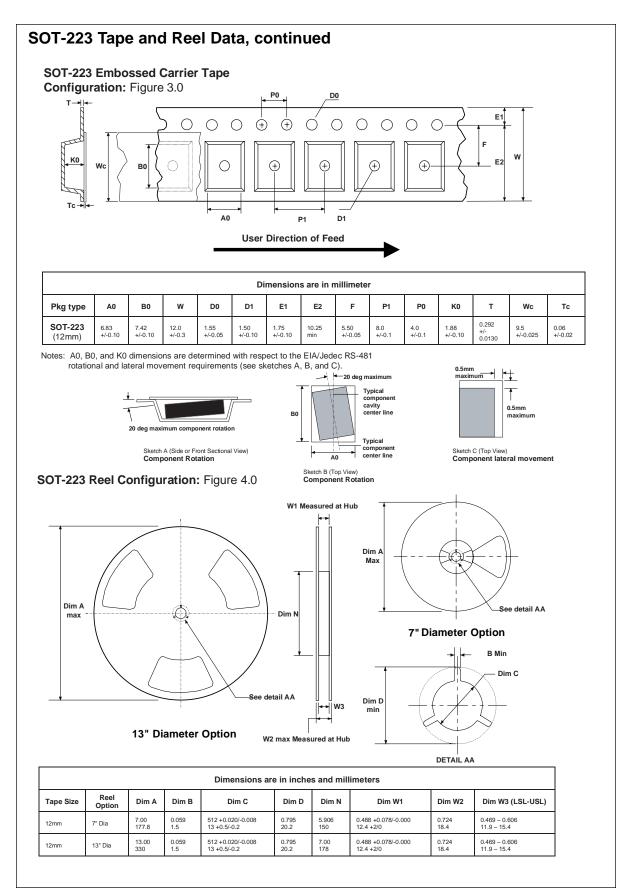
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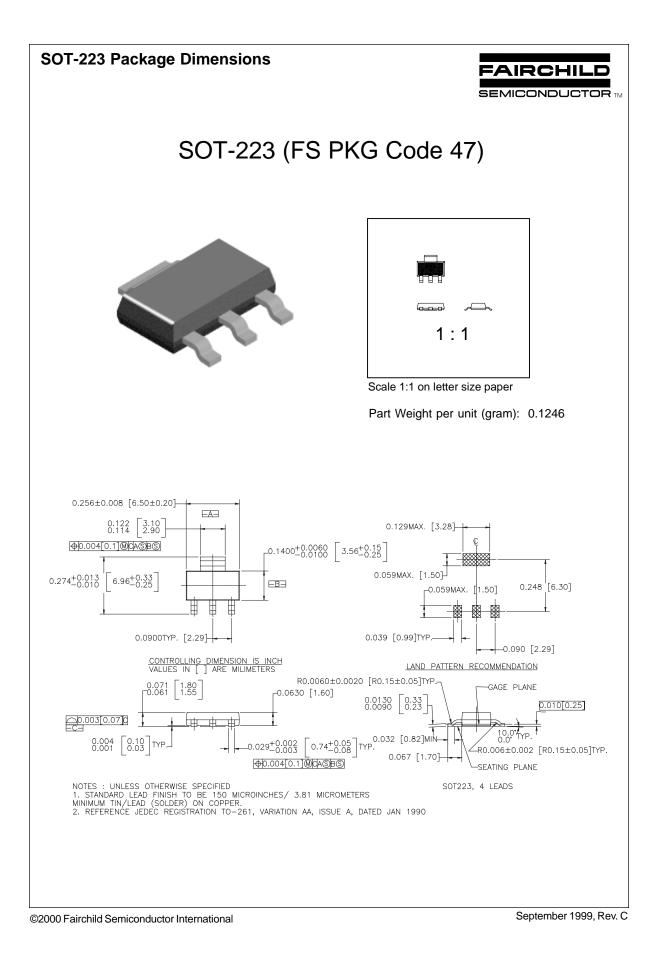




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